

## 0.04 - 65GHz Broadband MMIC Amplifier with PLFX

### Application

The UAPM65S2C Broadband MMIC Amplifier with PLFX is designed for general purpose broadband applications in RF and microwave communications, test equipment and military systems. By using specific external components, the bandwidth of operation can be extended below 40MHz.

### Description

The UAPM65S2C is an eight stage traveling wave amplifier. The amplifier features Centellax PLFX (Passive Low Frequency eXtension) circuitry designed to reduce the integration cost of the amplifier. PLFX isolates the amplifier from bias inductor resonances, allowing use of a less-expensive coil.

### Features

The UAPM65S2C has >30dB dynamic gain control, includes a temperature-referenced power detector output, and features patented PLFX technology.



### Device Highlights

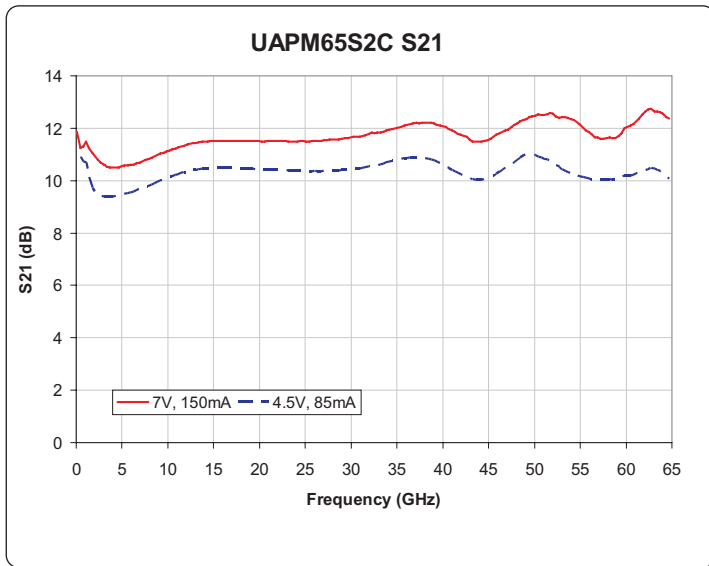
- Integrated PLFX technology:
  - Allows use of less-expensive coil
- Excellent 0.04-50GHz performance:
  - $10 \pm 1.25$ dB gain
  - 18dBm  $P_{sat}$ , 15dBm  $P_{-1dB}$
  - 10dB return loss, 25dB isolation
- Broadband 65GHz performance:
  - $10 \pm 1.25$ dB gain, 9dB return loss
  - >30dB dynamic gain control
- Integrated power detector
- 100% DC, RF, and visually tested
- Size: 1640x920um (64.6x36.2mil)

## Key Specifications

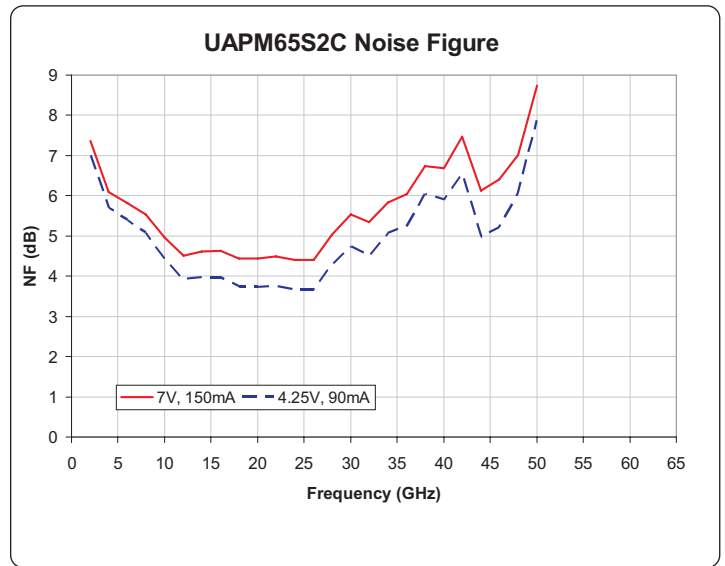
Vdd=7V, Idd=150mA, Zo=50Ω

Specifications pertain to wafer measurements with RF probes and DC bias cards @ 25°C

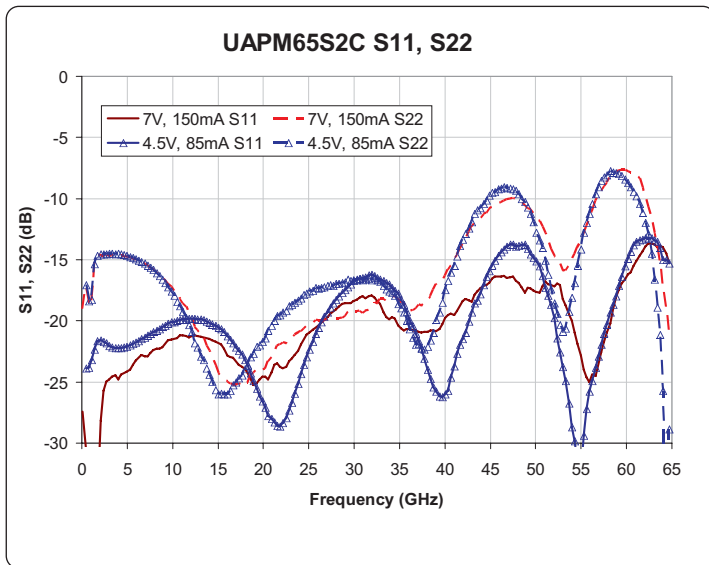
Parameter	Description	1.5 - 40GHz			0.04 - 50GHz			0.04 - 65GHz		
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max
S21 (dB)	Small Signal Gain	9.5	10.25		8.5	10		6	10	
Flatness (±dB)	Gain Flatness		1.0	1.25		1.25	1.75		1.25	1.75
S11 (dB)	Input Match		-18	-14		-16	-12		-14	-10
S22 (dB)	Output Match		-14	-12		-10	-7		-9	-6
S12 (dB)	Reverse Isolation		-32	-27		-25	-20		-20	-15
$P_{-1dB}$ (dBm)	1dB Compressed Output Power	15.5	17		13.5	15				
$P_{sat}$ (dBm)	Saturated Output Power	18.5	20			18				
NF (dB)	Noise Figure		7.5			9				
RF <sub>det</sub> (mV/mW)	RF Detector Sensitivity		0.7			0.7				



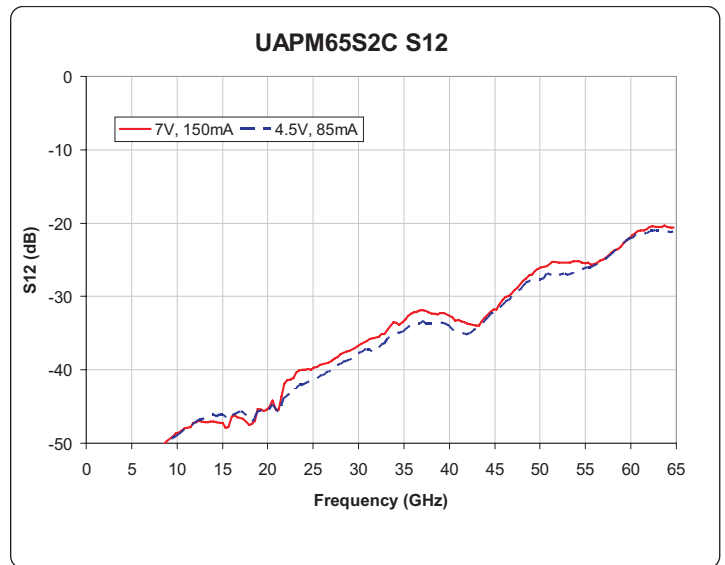
Typical IC performance measured on-wafer



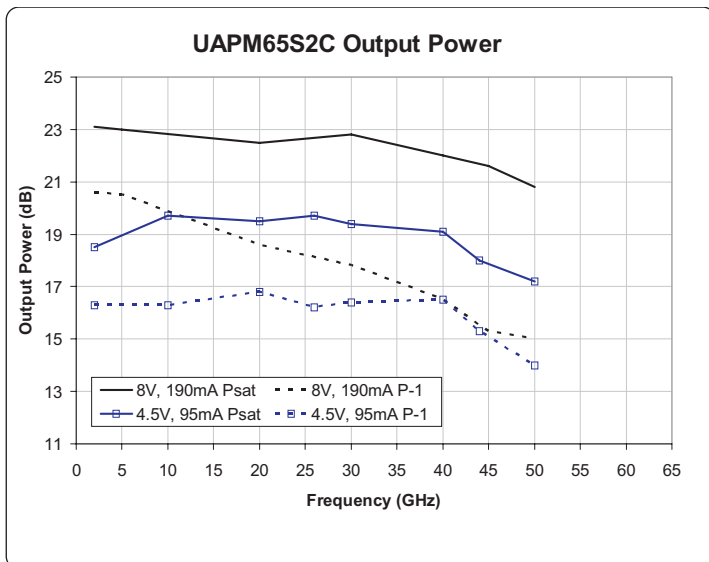
Typical IC performance with package de-embedded



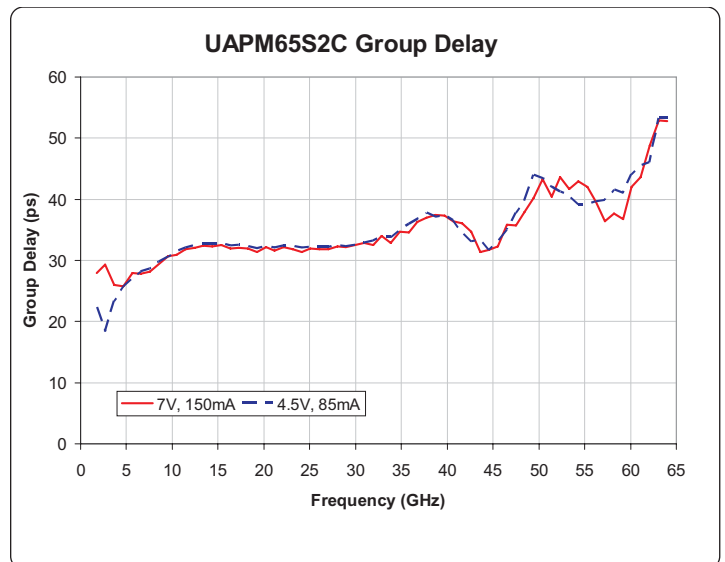
Typical IC performance measured on-wafer



Typical IC performance measured on-wafer



Typical IC performance measured on-wafer



Typical IC performance measured on-wafer

Typical measurement data is available upon request. Email [support@centellax.com](mailto:support@centellax.com) for more information.

## Supplemental Specifications

Parameter	Description	Min	Typ	Max
Vdd	Drain Bias Voltage	—	7V	8.2V
Idd	Drain Bias Current	—	150mA	250mA
Vg1	1st Gate Bias Voltage	-4V	—	+0.5V
Vg2	2nd Gate Bias Voltage	Vdd-Vg2<7V	N/C	+4V
P <sub>in</sub>	Input Power (CW)			22dBm
P <sub>dc</sub>	Power Dissipation		1.05W	
T <sub>ch</sub>	Channel Temperature			150°C
Θ <sub>ch</sub>	Thermal Resistance (T <sub>case</sub> =85°C)		19°C/W	

### DC Bias

The UAPM65S2C features a patented on-chip passive bias circuit called 'PLFX'. This circuit isolates the amplifier from bias coil resonances above 14GHz, allowing the use of less expensive coils; traditional biasing requires bias coils with self-resonances outside the operating range of the amplifier.

The device is biased by applying a positive voltage to the drain (Vdd), then setting the drain current (Idd) using a negative voltage on the gate (Vg1). The nominal bias is Vdd=7V, Idd=150mA.

Improved performance can be achieved with gate bias adjust-

ment; use the drain termination bypass to alter the output voltage (detected from the drain sense).

### Gain Control

Dynamic gain control is available when operating the amplifier in the linear gain region. Negative voltage applied to the second gate (Vg2) reduces amplifier gain.

### RF Power Detection

RF output power can be calculated from the difference between the RF detector voltage and the DC detector voltage, minus a DC offset. Please consult the application note available on the Centellax website.

## Low-Frequency Use

The UAPM65S2C has been designed so that the bandwidth can be extended to low frequencies. The low end corner frequency of the device is primarily determined by the external biasing and AC coupling circuitry.

### Matching

The amplifier incorporates on-chip termination resistors on the RF input and output. These resistors are RF grounded through on-chip capacitors, which are small and become open circuits at frequencies below 1GHz.

A pair of gate and drain termination bypass pads are provided for connecting external capacitors required for the low frequency extension network. These capacitors should be 10x the value of the DC blocking capacitors.

### DC Blocks

The amplifier is DC coupled to the RF input and output pads; DC voltage on these pads must be isolated from external circuitry.

For operation above 2GHz, a series DC-blocking capacitor with minimum value of 20pF is recommended; operation above 40MHz requires a minimum of 120pF.

### Inductor Bias

DC bias applied to the drain (Vdd) must be decoupled with an off-chip RF choke inductor. The amount of bias inductance will determine the low frequency operating point. Inductive biasing can also be applied to the chip through the RF output.

For many applications above 2GHz, a bondwire from the Vdd pad will suffice as the biasing inductor. Ensure the correct bond length as shown in the assembly diagrams.

